

Description

The VST04N020 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

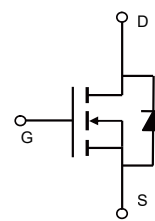
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS}=40V, I_D=120A$
 $R_{DS(ON)}=2.05m\Omega$ (typical) @ $V_{GS}=10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating



DFN5x6



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST04N020	VST04N020-D56	DFN5x6	-	-	-

Absolute Maximum Ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	120	A
Drain Current-Continuous($T_c=100^{\circ}C$)	$I_D(100^{\circ}C)$	84.8	A
Pulsed Drain Current (Package Limited)	I_{DM}	400	A
Maximum Power Dissipation	P_D	120	W
Derating factor		0.96	W/ $^{\circ}C$
Single pulse avalanche energy (Note 5)	E_{AS}	480	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	1.04	$^{\circ}C/W$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.8	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=60A$	-	2.05	2.4	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=60A$		56	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	1820	-	PF
Output Capacitance	C_{oss}		-	435	-	PF
Reverse Transfer Capacitance	C_{rss}		-	34	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=60A$ $V_{GS}=10V, R_G=1.6\Omega$	-	7	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	24	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=60A,$ $V_{GS}=10V$	-	24		nC
Gate-Source Charge	Q_{gs}		-	7		nC
Gate-Drain Charge	Q_{gd}		-	3.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=60A$	-		1.2	V
Diode Forward Current	I_S		-	-	120	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = I_S$ $di/dt = 100A/\mu s$ (Note3)	-		21	nS
Reverse Recovery Charge	Q_{rr}		-		60	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

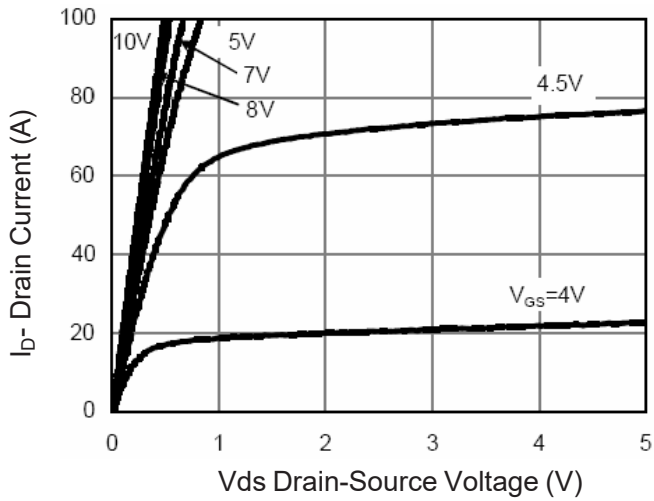


Figure 1 Output Characteristics

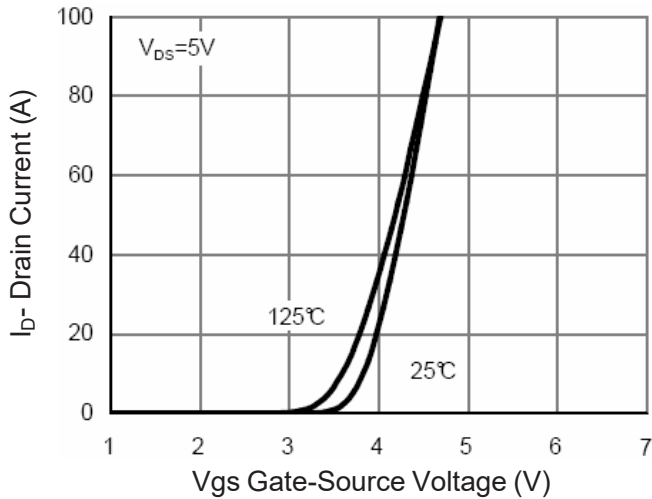


Figure 2 Transfer Characteristics

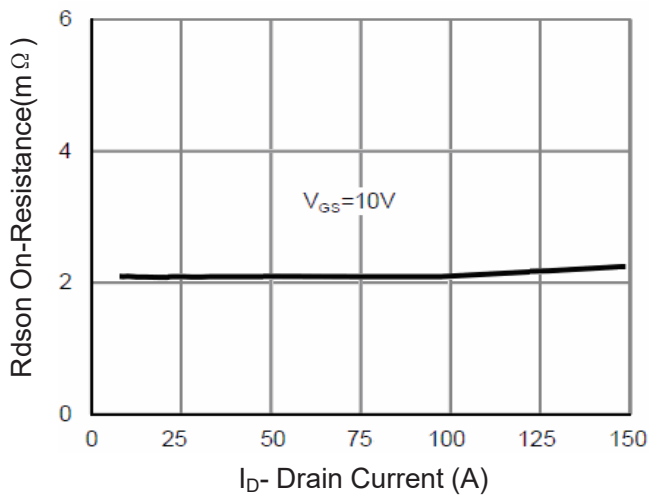


Figure 3 Rdson- Drain Current

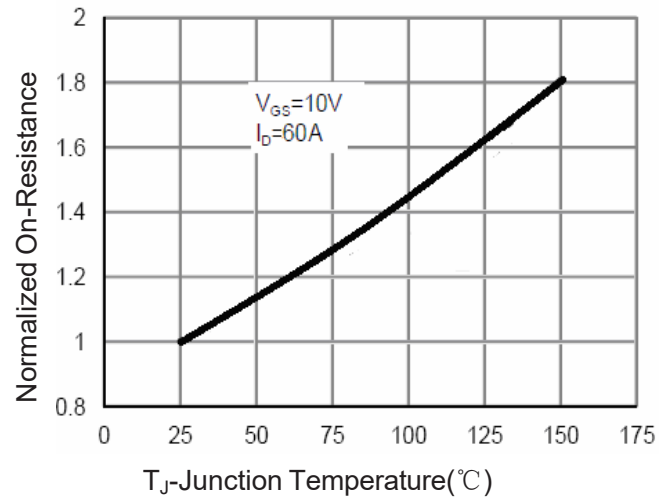


Figure 4 Rdson-Junction Temperature

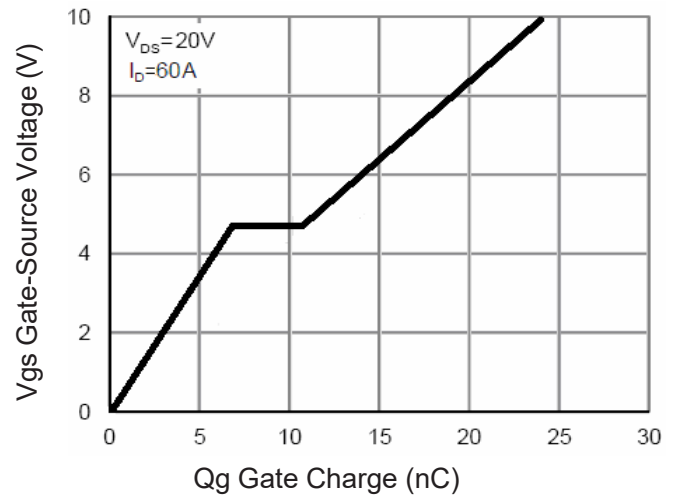


Figure 5 Gate Charge

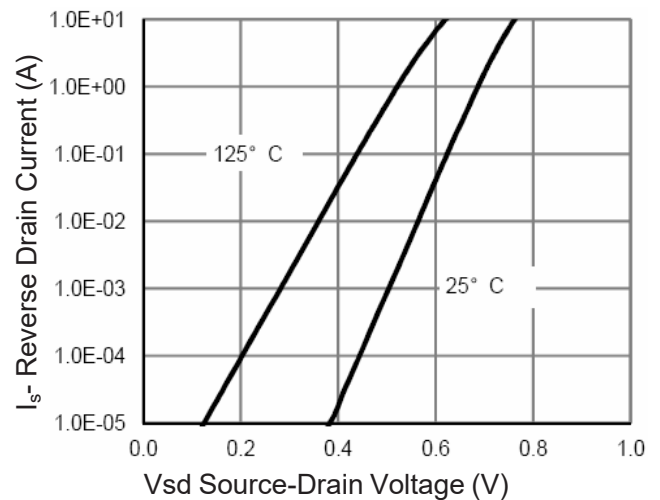
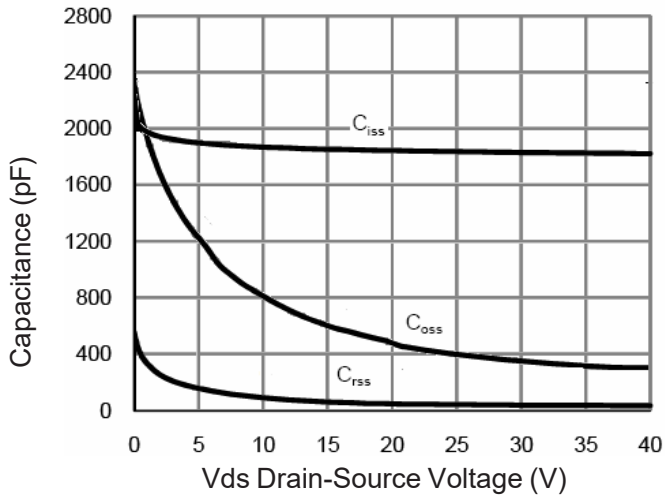
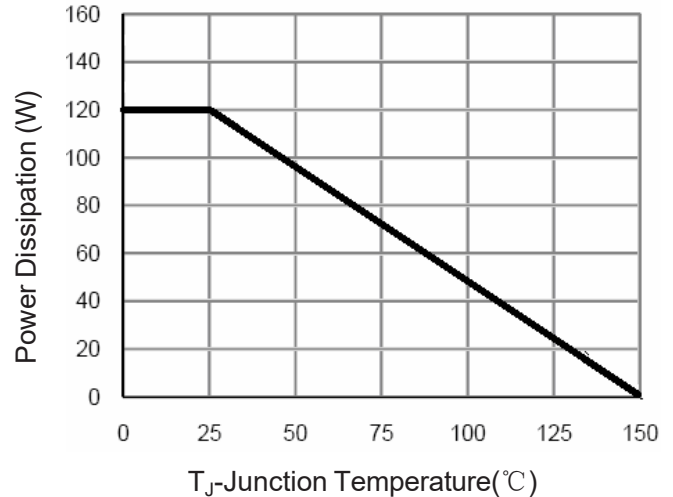
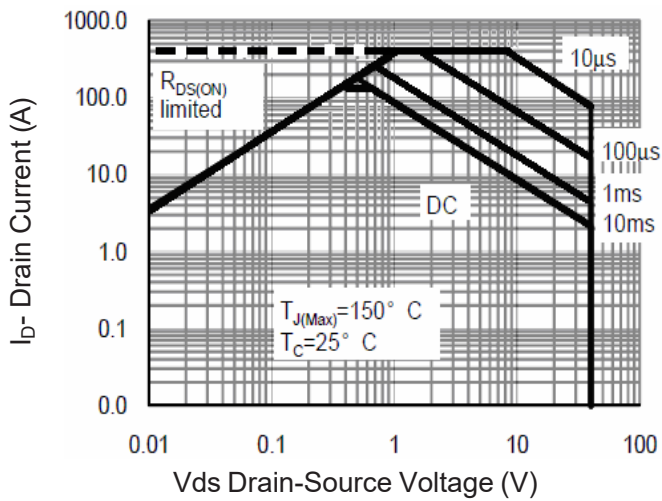
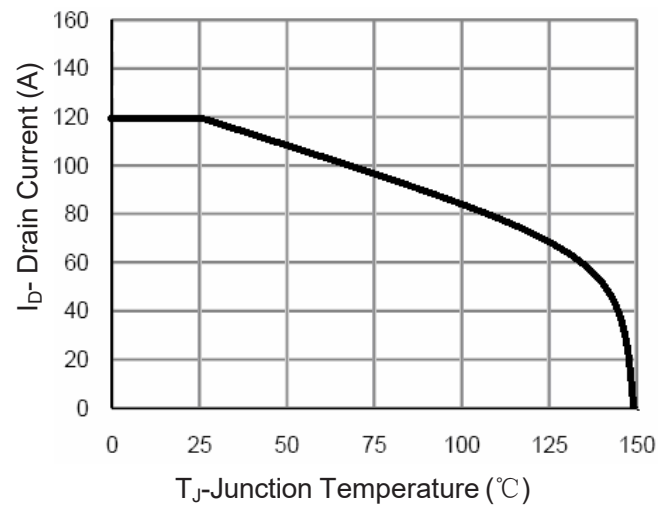
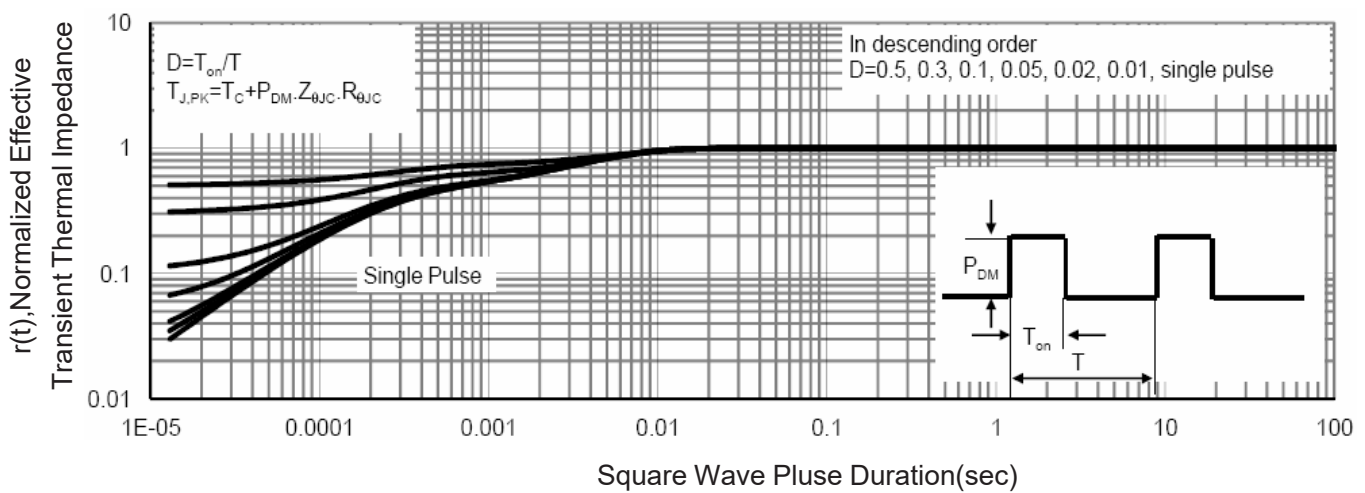


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance